



## **NXP Celebrates 60 Years of RF Innovation; Ramping Toward 5G at International Microwave Symposium**

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HONOLULU , June 05, 2017 (GLOBE NEWSWIRE) -- **IMS 2017** -- NXP Semiconductors N.V. (NASDAQ:NXPI), the No. 1 supplier of high-power RF power transistors, will showcase its new 5G cellular base station concept alongside many other innovative cellular infrastructure solutions and technologies at the International Microwave Symposium (IMS), June 4-9, at booth 1132. In addition, NXP will contribute a rich offering of technical content through its participation in [eight workshops and paper presentations](#) during the course of the conference.

"5G is likely the single greatest technological innovation we will see in the foreseeable future in terms of its impact on society, enabling the future connected world," said Paul Hart, SVP and GM of RF Power at NXP. "At NXP, we have been innovating in this space for 60 years. At this year's IMS, we are excited to demonstrate these key enablers of 5G with our new GaN and silicon LDMOS products."

### **Establishing the 5G Infrastructure**

As the number of connected devices and smart applications continues to increase, NXP is providing purpose-built power amplifier (PA) solutions to support the size, power and frequency bands needed for 5G new radio (NR). According to a recently published IHS Markit [study](#), the adoption of 5G mobile technology could enable \$12.4 trillion of global economic output by 2035. NXP's RF high-performance cellular infrastructure products and technologies are already being used by top cellular infrastructure OEMs in their product designs for 5G NR. For more information on NXP's 5G efforts, visit [www.nxp.com/5Gradio](http://www.nxp.com/5Gradio).

### **Driving Next-generation Gallium Nitride (GaN) Technology from Art to Mainstream**

Spectrum expansion in the higher frequency bands along with the need for larger bandwidths to aggregate more carriers across diverse bands has accelerated the adoption of GaN in base station radios. According to [ABI Research](#), RF power GaN devices are expected to represent nearly 25 percent of all high-power semiconductors for mobile wireless infrastructure in 2017. With the adoption of 5G NR standards, the use of GaN is expected to become even more widespread in the future.

NXP is committed to the successful deployment of best-in-class GaN technology. From 2015 to 2016, NXP more than doubled its offering of GaN RF transistors. By continuing to increase its GaN offerings in 2017, NXP will not only be able to better serve the cellular infrastructure markets, but also offer full GaN lineups in a variety of power ranges for industrial and defense markets. For more information on NXP's GaN technology capabilities, visit [www.nxp.com/REFGaN](http://www.nxp.com/REFGaN). The latest innovations in GaN will also be on display in NXP's booth at IMS.

### **NXP Airfast Third-generation Laterally Diffused Metal Oxide Semiconductor (LDMOS) Products**

RF silicon LDMOS products continue to be the most widely deployed in cellular base stations. With NXP's strong market share and leadership, it has made major advancements in every generational iteration of its LDMOS product line. The latest generation offers significant performance improvements in efficiency, gain, thermal performance and signal bandwidth. These enhancements are intended to support the requirements of next-generation macro base stations and smart mobility solutions for 5G. For more information on NXP's Airfast solutions, visit [www.nxp.com/Airfast](http://www.nxp.com/Airfast).

### **NXP Small Cell Solutions for Improved Coverage and Capacity**

In addition to macro cells, network densification using small cells is considered necessary by wireless operators to improve coverage, capacity and speeds on their next-generation networks.

NXP's solutions for small cells provide high levels of integration and small form factors that enable these system-level improvements. With a comprehensive lineup of high-power symmetric and asymmetric ICs from 700 to 3800 MHz frequency, NXP has products to fit deployments from 3G to 4G to 5G. For more information on NXP's small cell solutions, visit [www.nxp.com/RFoutdoorsmallcell](http://www.nxp.com/RFoutdoorsmallcell).

NXP is also working with industry partners including [Analog Devices Inc.](#) and [NanoSemi Inc.](#) to provide complete linearized solutions. For information on test results and a product demonstration, please visit [www.analog.com/RadioVerse](http://www.analog.com/RadioVerse) or IMS booth 1032 and [www.nanosemitech.com/evaluation-platform](http://www.nanosemitech.com/evaluation-platform) or IMS booth 2030.

For more information, visit [www.nxp.com/RF](http://www.nxp.com/RF).

### **About NXP Semiconductors**

NXP Semiconductors N.V. (Nasdaq:NXPI) enables secure connections and infrastructure for a smarter world, advancing solutions that make lives easier, better and safer. As the world leader in secure connectivity solutions for embedded applications, NXP is driving innovation in the secure connected vehicle, end-to-end security & privacy and smart connected solutions markets. Built on more than 60 years of combined experience and expertise, the company has 31,000 employees in more than 33 countries and posted revenue of \$9.5 billion in 2016. Find out more at [www.nxp.com](http://www.nxp.com).

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